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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number	10550853	
	Filing Date	2005-09-22	
	First Named Inventor	MEUNIER-BEILLARD, PHILIPPE	
	Art Unit	2823	
	Examiner Name	NGUYEN, KHIEM D	. <u></u> .
	Attorney Docket Num	per NL03 0357 US1	

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Examiner Initial*	Cite No	Patent Number	Kind Code <sup>1</sup>	1995-01-03		Name of Patentee or Applicant of cited Document		Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear	
	1	5378651	А			AGNELLO, PA	.UL D.; ET AL		
	2	6251188	B1	2001-06	i-26	HASHIMOTO,	TSUYOSHI; ET AL		
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	1	20030003646	A1			WIEBE BARTELD DE BOER			
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	1	0459122	EP	A2		1991-12-04	INTERNATIONAL BUSINESS MACH CORPORATION	INES	
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	1	AGNELLO, P.D., ET AL; "HEAVY ARSENIC DOPING OF SILICON GROWN BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 60 (4); JANUARY 27, 1992; PAGES 454 - 456					
	2	AGNELLO, P.D., ET AL; "SILICON EPITAXY FROM SILANE BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 61 (11); SEPTEMBER 14, 1992; PAGES 1298 - 1300					
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